

**1. Scope :**

This specification applies to P/N silicon TVS diode chips,  
Device NO. SD-11308

**2. Structure :**

- 2-1. Planar type : P/N Diode.
- 2-2. Electrodes :  
Top side : Aluminum alloy.  
Back side : Gold layer.

**3. Size :**

- 3-1. Chip size : 15.4 mils x 10.6 mils (0.390 mm x 0.270 mm ).
- 3-2. Chip thickness :  $5.9 \pm 1.0$  mils ( $0.150 \pm 0.0254$  mm )
- 3-3. Bonding pad : 10.6 mils x 5.9 mils (0.270 mm x 0.150 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

**4. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Current	$I_R$	$V_R=5V$ $E_e=0mW/cm^2$			2000	nA
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R=5mA$ $E_e=0mW/cm^2$	7		9	V
Forward Voltage	$V_f$	$I_F=10mA$ $E_e=0mW/cm^2$			1.2	V

